

preliminary

Туре	Ag [*] Aİ [*]	V _{DRM} / V _{RRM}	V _{DSM} / V _{RSM} [V]	/_{Т(AV)} [A]	Chip Size [mm] x [mm]	Package Options	•
CWP 30-	12 🗹 🗸	1200	1300	48	7.60 7.60	sawn on foil unsawn wafer in waffle pack	
	*Frontside options					*Please contact IXYS chip sales	

Mechanical Parameters

Area active Area total Wafer size Ø Thickness Material Max. possible chips per wafer Passivation front side Metallization top side top side Recom. wire bonds (AI) * = Stitchbonds Number / Ø [µm] Metallization backside Reject Ink Dot Size Recom. Storage Environment sawn on foil unsawn wafer in waffle pack

cm² 0.31 0.58 cm² 150 mm 290 μm Si 227 Glassivation solderable: Ti / Ni / Ag * bondable: ΑI Cathode Gate 7* / 500 1 / 500 solderable (only): Ti / Ni / Ag *

in org. container, in dry nitrogen < 6 month in org. container, in dry nitrogen < 2 year in org. container, in dry nitrogen < 2 year $\mathsf{T}_{\mathsf{stg}} \qquad \quad \mathsf{-40} \dots \quad \mathsf{40} \quad {}^{\circ}\mathsf{C}$

Ø 0.4-1.0 mm

Features

- planar passivated with guardring and channelstopper
- Planar front and back surface
- Non-structured anode contact on full area bottom side

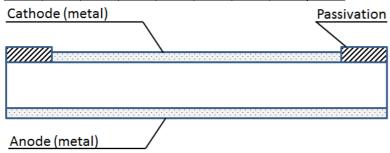
Applications

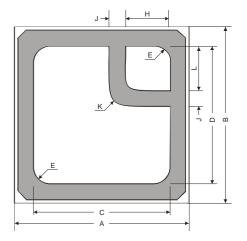
- DC motor control
- AC power control
- Softstart AC motor controller
- Light, heat and temperature control

*Sinterable top/bottom side on request

Dimensions

В С D Е Н Κ J L [mm] [mm] [mm] [mm] [mm] [mm] [mm] [mm] [mm] 6.00 0.40 7.60 7.60 6.00 0.34 1.50 0.40 1.50





Thyristor Chip

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		Ratings			
Symbol	Conditions	min.	typ.	max.	
I _R	$V_D = Vr = Vrr$	••		0.05	
V ₇	I _T =115 A	••	1	5 1.33	\
v	For power loss	T _{V,I} = 125 °C s calculations only	- (1.32 0.9	\ \
ν _{το} r _τ	$T_{VJ} = 150 ^{\circ}\text{C}$	s calculations only		3.50	-
V _{G7}	$V_D = 6 \text{ V}$	T _{vJ} = 25°C	10	1.5	\
		$T_{VJ} = -40$ °C		1.6	١
l _{et}		$T_{vJ} = 25^{\circ}C$ 25 $T_{vJ} = -40^{\circ}C$		38 80	
V _{GD}	T _{v,i} = 150 °C			0.2	١
I _{GD}	V 0	Divin		5	m <i>P</i>
I <u>,</u>	t _p =10 μs	$T_{VJ} = 25^{\circ}C$ $I_{G} = 0.45 \text{ A}$ $di_{G}/dt = 0.45 \text{ A}/\mu\text{s}$		150	m/
I _H	R _{GK} = ∞	$T_{V,I} = 25^{\circ}C$ $V_{D} = 6 \text{ V}$		100	m/
t _{gd}	$V_D = \frac{1}{2} V_{DRM}$			2	μ
t _a		$di_{G}/dt = 0.5 \text{ A/}\mu$ $I_{T} = 40 \text{ A}$ -di/dt = 20 A/ μ s		150	μ
•	$t_p = 200 \mu s$	$dv/dt = V/\mu s V_D = \frac{2}{3} V drm T_{V,J} = 125 °C$			
(di/dt) _{cr}	repetitive	$I_{\tau} = 75$ A		150	A/µs
	non repetitive	·		500	A/µs
	5	$T_{VJ} = 150 ^{\circ}\text{C}$ $di_{G}/dt = 0.45 \text{A/µs}$			
/ah	$I_{\rm G} = 0.45 \text{ A}$ $T_{\rm MI} = 150 ^{\circ}\text{C}$			1000	\//
(dv/dt) _{cr}	$R_{GK} = 130^{\circ} C$	$V_{DR} = \frac{2}{3} V_{DRM}$ method 1 (linear voltage rise)		1000	V/με
P _{GM}	T _{v.i} = 150 °C	$t_p = 30 \mu s$		10	W
	VJ	$t_p = 3E \mu s$		5	W
P _{GAV}				0.5	W
V _{RGM}				10	٧
T _{VJ}		-40		150	°C
I _{T(AV)}	$T_{\rm C} = 75^{\circ}{\rm C}$	180° rect.		48	Δ
	$T_{VJ} = 125 ^{\circ}\text{C}$	180° sine		46	Δ
I _{TSM} *	T _{vJ} = 45°C	t = 10 ms (50) Hz, sine		1000	Α
	$V_R = 0 V$	t = 8.3 ms (60) Hz, sine		1100	Α
	T _{VJ} = 150 °C	t = 10 ms (50) Hz, sine		850	P
	$V_R = 0 V$	t = 8.3 ms (60) Hz, sine		920	Α
l²t *	$T_{VJ} = 45^{\circ}C$	t = 10 ms (50) Hz, sine		5000	Α :
	$V_R = 0 V$	t = 8.3 ms (60) Hz, sine		5022	As
	T _{VJ} = 150 °C	t = 10 ms (50) Hz, sine		3613	A s
	$V_R = 0 V$	t = 8.3 ms (60) Hz, sine		3513	As
R _{thJC} *	DC current		0.85		K/W

^{*} Data according to assembled product (solderable) tbd

Data according to IEC 60747

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CWP 30-12

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Should you intend to use the product in aviation applications, in health or life endangering or life support applications, please notify. For any such applications we urgently recommend

- to perform joint risk and quality assessments;
- the conclusion of quality agreements;
- to establish joint measures to ensure application specific product capabilities and notify that IXYS may delivery dependent on the realization of any such measures.